

NPN SILICON POWER TRANSISTOR ARRAY LOW SPEED SWITCHING USE (DARLINGTON TRANSISTOR) INDUSTRIAL USE

DESCRIPTION

The μ PA1478 is NPN silicon epitaxial Darlington Power Transistor Array that built in Surge Absorber and 4 circuits designed for driving solenoid, relay, lamp and so on.

FEATURES

- Surge Absorber (Zener Diode) built in.
- Easy mount by 0.1 inch of terminal interval.
- High h_{FE} for Darlington Transistor.

ORDERING INFORMATION

Part Number	Package	Quality Grade
μ PA1478H	10 Pin SIP	Standard

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^\circ\text{C}$)

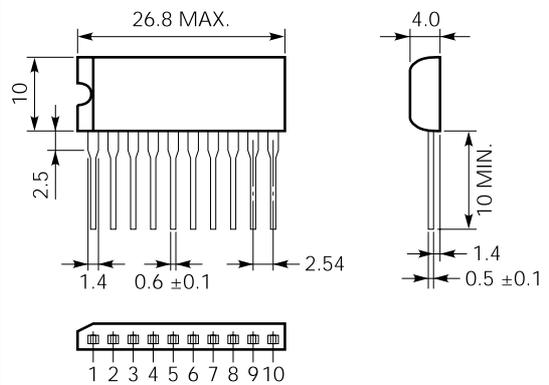
Collector to Base Voltage	V_{CBO}	31 ± 4	V
Collector to Emitter Voltage	V_{CEO}	31 ± 4	V
Emitter to Base Voltage	V_{EBO}	7	V
Surge Sustaining Energy	$E_{CEO(SUS)}$	40	mJ/unit
Collector Current (DC)	$I_{C(DC)}$	± 2	A/unit
Collector Current (pulse)	$I_{C(pulse)^*}$	± 4	A/unit
Total Power Dissipation	P_{T1}^{**}	3.5	W
Total Power Dissipation	P_{T2}^{***}	28	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

* $PW \leq 300\ \mu s$, Duty Cycle $\leq 10\%$

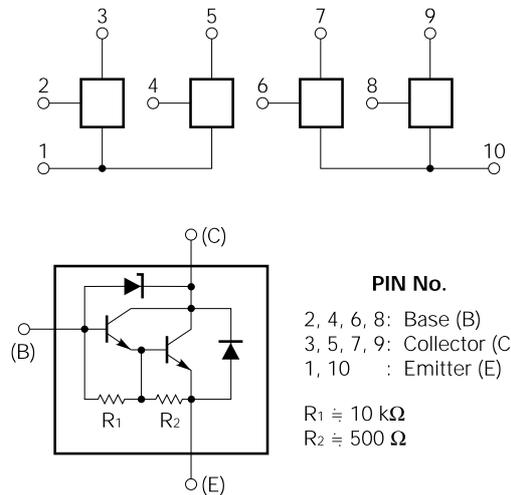
** 4 Circuits, $T_a = 25\text{ }^\circ\text{C}$

*** 4 Circuits, $T_c = 25\text{ }^\circ\text{C}$

PACKAGE DIMENSION (in millimeters)



CONNECTION DIAGRAM



The information in this document is subject to change without notice.